

NVMJS1D0N04C

MOSFET – Power, Single N-Channel

40 V, 0.92 mΩ, 300 A

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- LFPK8 Package, Industry Standard
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	40	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Notes 1, 3)	Steady State	T _C = 25°C	I _D	300	A
		T _C = 100°C		212	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	166	W
		T _C = 100°C		83	
Continuous Drain Current R _{θJA} (Notes 1, 2, 3)	Steady State	T _A = 25°C	I _D	46	A
		T _A = 100°C		32	
Power Dissipation R _{θJA} (Notes 1, 2)		T _A = 25°C	P _D	3.9	W
		T _A = 100°C		1.9	
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	900	A
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to + 175	°C
Source Current (Body Diode)			I _S	158	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 34 A)			E _{AS}	578	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	36	

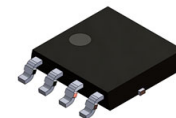
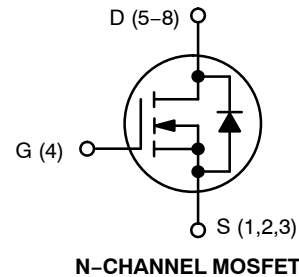
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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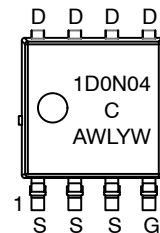
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	0.92 mΩ @ 10 V	300 A



LFPK8
CASE 760AA

MARKING DIAGRAM



1D0N04C = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
W = Work Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMJS1D0N04C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			16		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25 °C		10	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 190 μA	2.5		3.5	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-7		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 50 A		0.76	0.92	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 50 A		190		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		6100		pF
Output Capacitance	C _{OSS}			3400		
Reverse Transfer Capacitance	C _{RSS}			70		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 32 V; I _D = 50 A		86		nC
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 10 V, V _{DS} = 32 V; I _D = 50 A		18		
Gate-to-Source Charge	Q _{GS}			28		
Gate-to-Drain Charge	Q _{GD}			14		
Plateau Voltage	V _{GP}			4.9		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 50 A, R _G = 2.5 Ω		54		ns
Rise Time	t _r			162		
Turn-Off Delay Time	t _{d(OFF)}			227		
Fall Time	t _f			173		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 50 A	T _J = 25°C		0.8	1.2	V
			T _J = 125°C		0.65		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 50 A			91		ns
Charge Time	t _a				42		
Discharge Time	t _b				49		
Reverse Recovery Charge	Q _{RR}				159		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

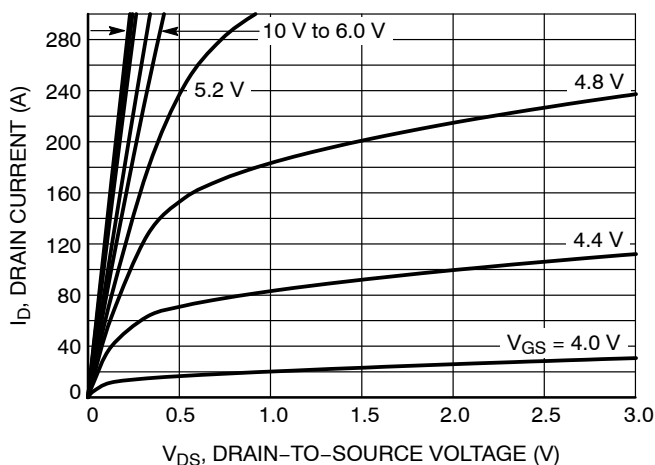


Figure 1. On-Region Characteristics

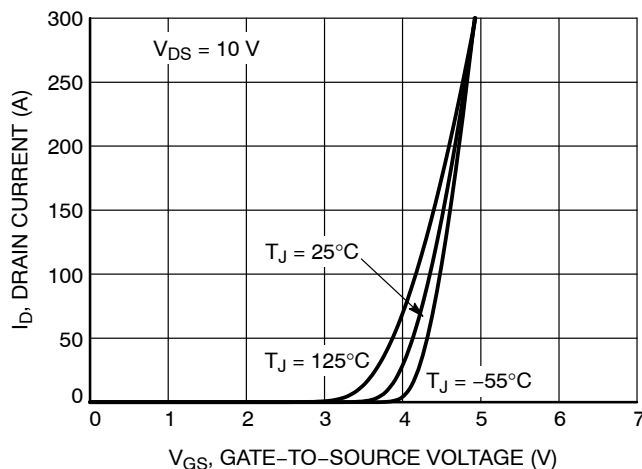


Figure 2. Transfer Characteristics

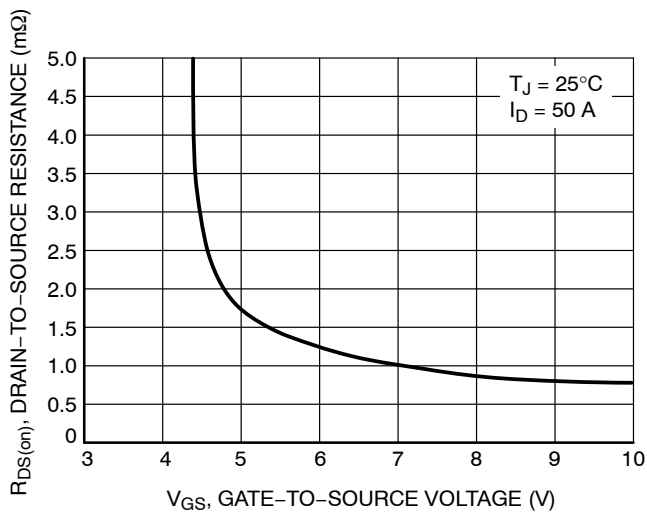


Figure 3. On-Resistance vs. Gate-to-Source Voltage

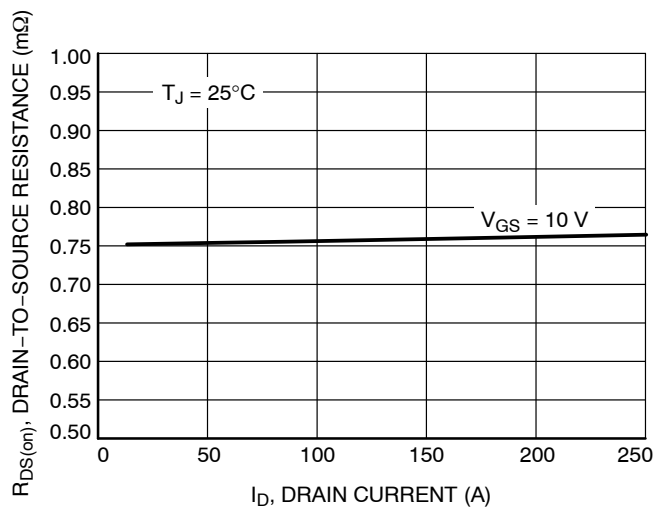


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

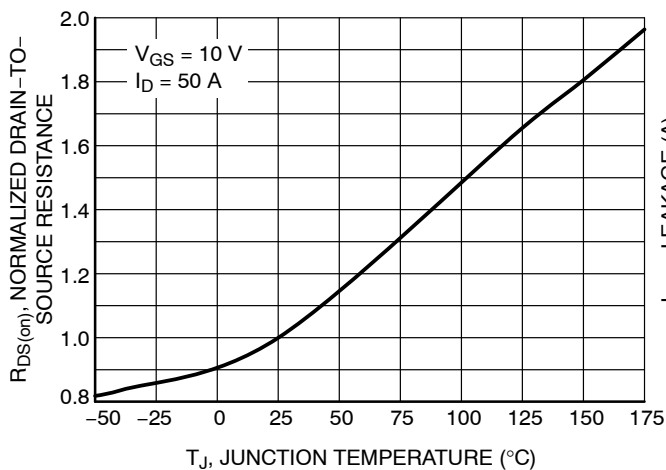


Figure 5. On-Resistance Variation with Temperature

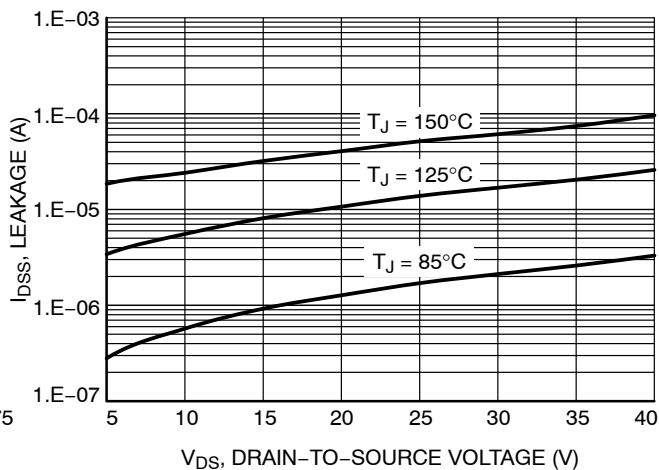


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

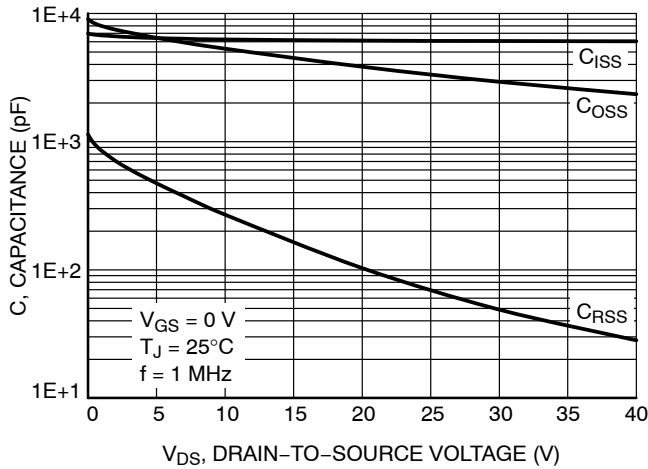


Figure 7. Capacitance Variation

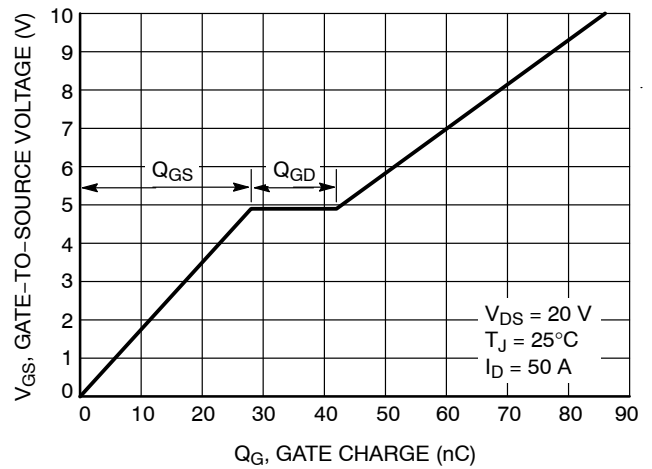


Figure 8. Gate-to-Source Voltage vs. Charge

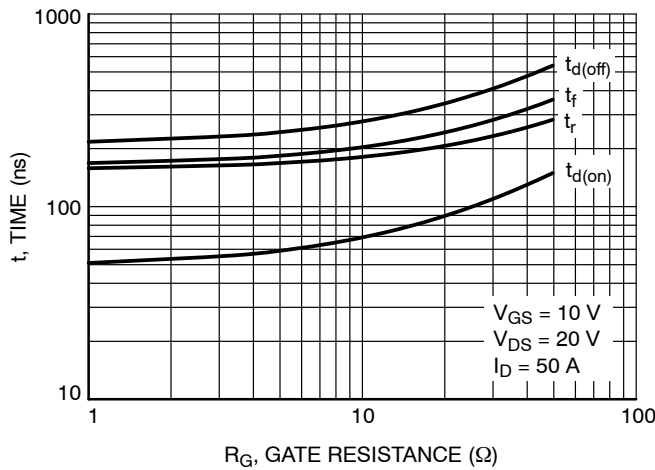


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

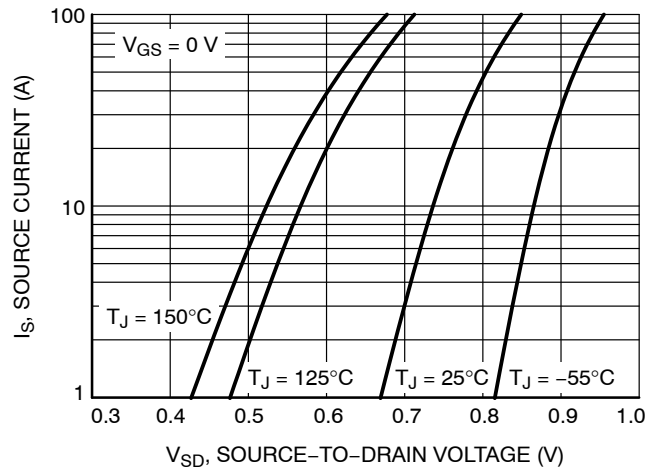


Figure 10. Diode Forward Voltage vs. Current

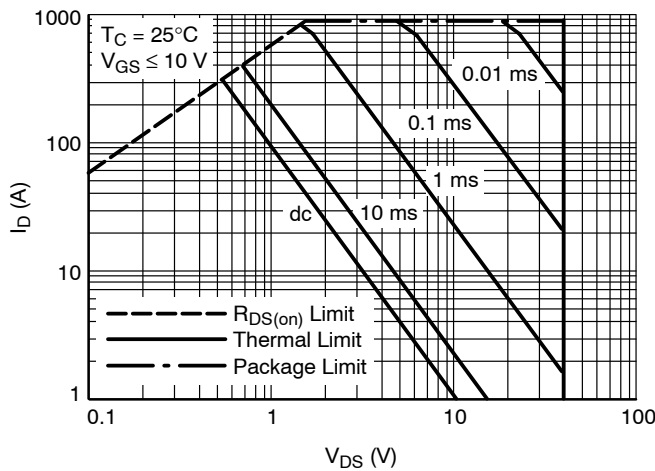


Figure 11. Safe Operating Area

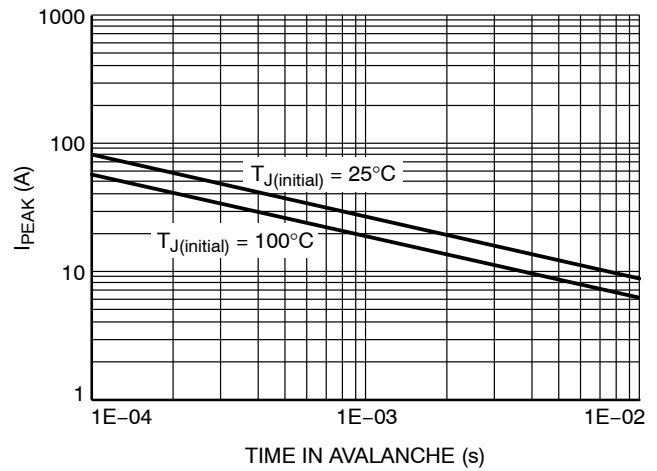


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

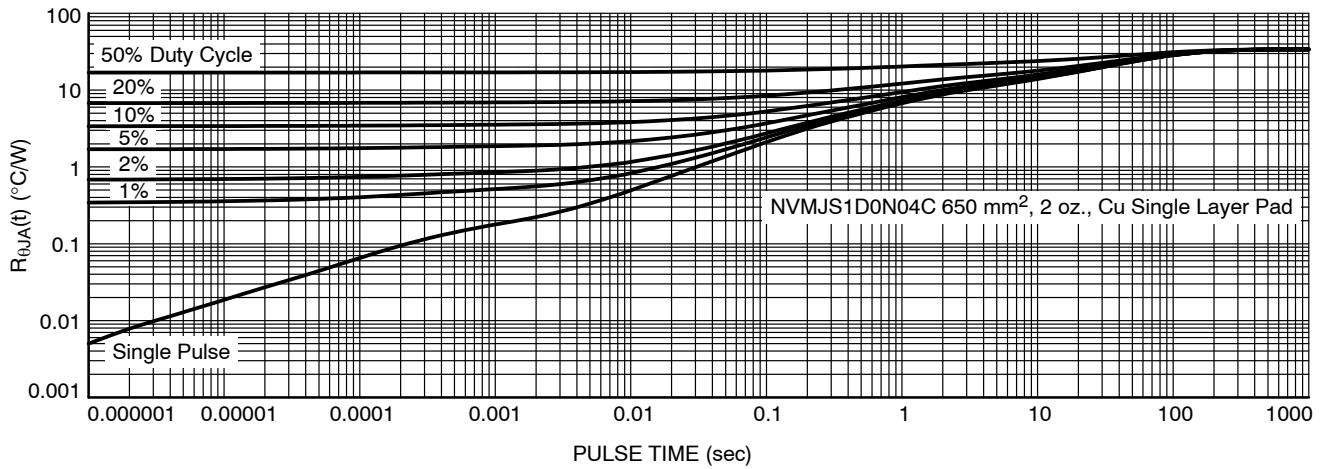


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

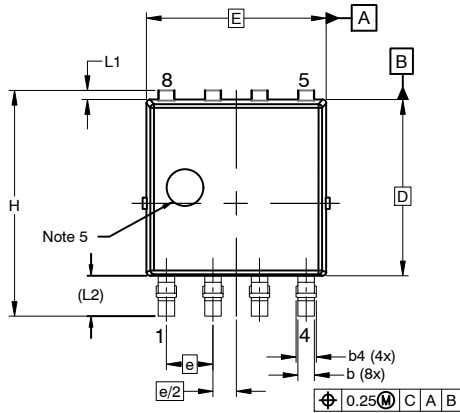
Device	Marking	Package	Shipping [†]
NVMJS1D0N04CTWG	1D0N04C	LFPAK8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

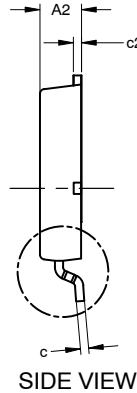


LPAK8 4.90x4.80x1.12MM, 1.27P
CASE 760AA
ISSUE D

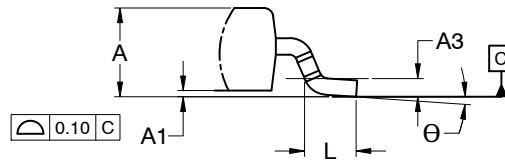
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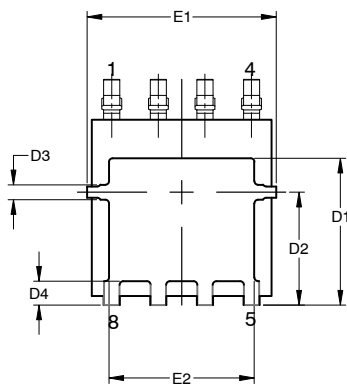
TOP VIEW



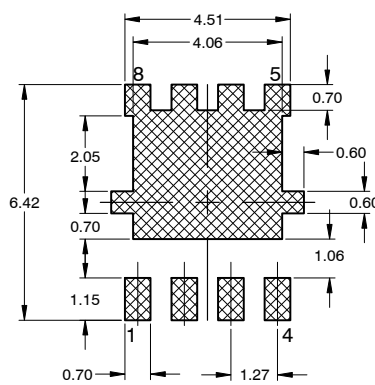
SIDE VIEW



DETAIL 'A'



BOTTOM VIEW



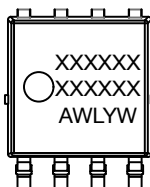
RECOMMENDED LAND PAD

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. OPTIONAL MOLD FEATURE.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 BSC		
b	0.40	0.45	0.50
b4	0.45	0.55	0.65
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.70	4.80	4.90
D1	3.80	4.00	4.20
D2	2.98	3.08	3.18
D3	0.30	0.40	0.50
D4	0.55	0.65	0.75
E	4.80	4.90	5.00
E1	5.05	5.15	5.25
E2	3.91	3.96	4.01
e	1.27 BSC		
e/2	0.635 BSC		
H	6.00	6.15	6.30
L	0.50	0.70	0.90
L1	0.15	0.25	0.35
L2	1.10 REF		
Θ	0°	4°	8°

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
 A = Assembly Location
 WL = Wafer Lot
 Y = Year
 W = Work Week

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Some products may not follow the Generic Marking.

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DESCRIPTION:	LPAK8 4.90x4.80x1.12MM, 1.27P	PAGE 1 OF 1

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